N *National Semiconductor*

74LCX16501
18-Bit Universal Bus Transceivers
with 5V Tolerant Inputs and Outputs

General Description

These 18-bit universal bus transceivers combine D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A bus data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. Output-enable OEAB is active-high. When OEAB is high, the outputs are active. When OEAB is low, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, and CLKBA. The output enables are complementary (OEAB is active high and $\overline{OEBA}$ is active low).

To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

Features

- 6.0 ns t_{PD} max, 20 μA I_{CCQ} max
- 5V tolerant inputs and outputs
- Power down high impedance inputs and outputs
- Supports live insertion/withdrawal
- 2.0V–3.6V V_{CC} supply operation
- ±24 mA output drive
- Implements patented Quiet Series™ noise/EMI reduction circuitry
- Functionally compatible with 74 series 16501
- Latch-up performance exceeds 500 mA
- ESD performance:
  Human body model > 2000V
  Machine model > 200V

Connection Diagram

Pin Assignment for SSOP and TSSOP

OEAB	1	56	GND
LEAB	2	55	CLKAB
A_1	3	54	B_1
GND	4	53	GND
A_2	5	52	B_2
A_3	6	51	B_3
V_{CC}	7	50	V_{CC}
A_4	8	49	B_4
A_5	9	48	B_5
A_6	10	47	B_6
GND	11	46	GND
A_7	12	45	B_7
A_8	13	44	B_8
A_9	14	43	B_9
A_{10}	15	42	B_{10}
A_{11}	16	41	B_{11}
A_{12}	17	40	B_{12}
GND	18	39	GND
A_{13}	19	38	B_{13}
A_{14}	20	37	B_{14}
A_{15}	21	36	B_{15}
V_{CC}	22	35	V_{CC}
A_{16}	23	34	B_{16}
A_{17}	24	33	B_{17}
GND	25	32	GND
A_{18}	26	31	B_{18}
$\overline{OEBA}$	27	30	CLKBA
LEBA	28	29	GND
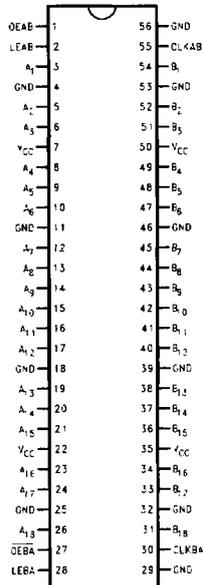
TL/F/12550–1

Function Table[†]

Inputs				Output
OEAB	LEAB	CLKAB	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	↑	L	L
H	L	↑	H	H
H	L	H	X	B_0[‡]
H	L	L	X	B_0[§]

†A-to-B data flow is shown; B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, and CLKBA.

‡Output level before the indicated steady-state input conditions were established.

§Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low.

Logic Diagram

To 17 Other Channels
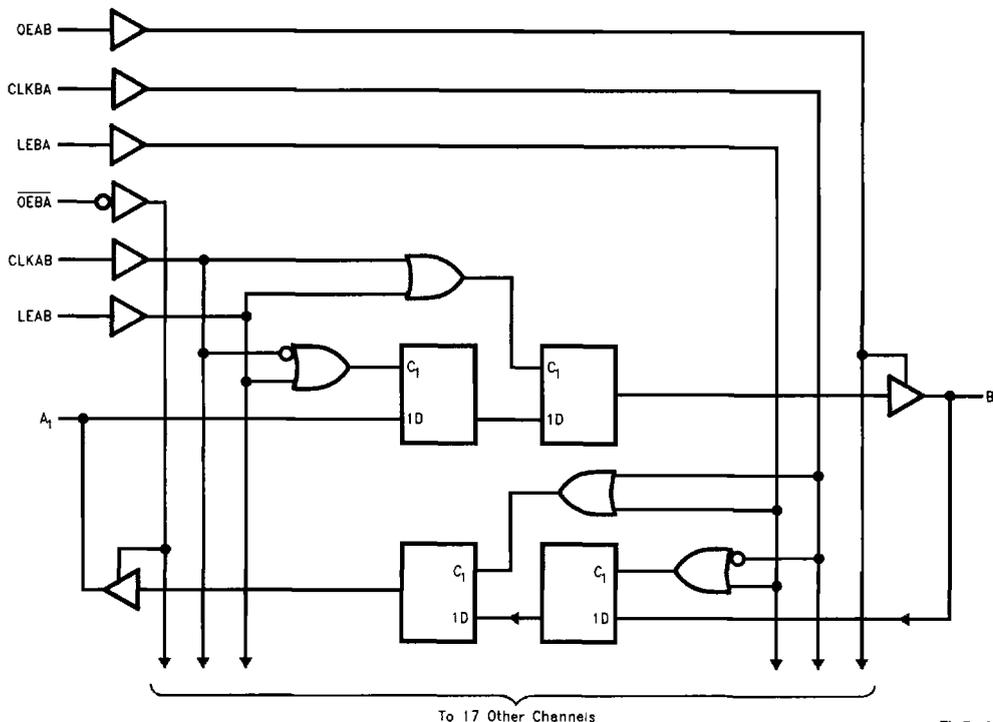
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Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Symbol	Parameter	Value	Conditions	Units
V_{CC}	Supply Voltage	−0.5 to +7.0		V
V_I	DC Input Voltage	−0.5 to +7.0		V
V_O	DC Output Voltage	−0.5 to +7.0	Output in TRI-STATE®	V
		−0.5 to V_{CC} + 0.5	Output in High or Low State (Note 2)	V
I_{IK}	DC Input Diode Current	−50	V_I < GND	mA
I_{OK}	DC Output Diode Current	−50	V_O < GND	mA
		+50	V_O > V_{CC}	
I_O	DC Output Source/Sink Current	±50		mA
I_{CC}	DC Supply Current per Supply Pin	±100		mA
I_{GND}	DC Ground Current per Ground Pin	±100		mA
T_{STG}	Storage Temperature	−65 to +150		°C

Note 1: The Absolute Maximum Ratings are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the Absolute Maximum Ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Note 2: I_O Absolute Maximum Rating must be observed.

Recommended Operating Conditions

Symbol	Parameter		Min	Max	Units
V_{CC}	Supply Voltage	Operating	2.0	3.6	V
		Data Retention	1.5	3.6	
V_I	Input Voltage		0	5.5	V
V_O	Output Voltage	HIGH or LOW State	0	V_{CC}	V
		TRI-STATE	0	5.5	
I_{OH}/I_{OL}	Output Current	V_{CC} = 3.0V − 3.6V		±24	mA
		V_{CC} = 2.7V		±12	
T_A	Free-Air Operating Temperature		−40	85	°C
$\Delta t/\Delta V$	Input Edge Rate, V_{IN} = 0.8V−2.0V, V_{CC} = 3.0V		0	10	ns/V

DC Electrical Characteristics

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = −40°C to +85°C		Units
				Min	Max	
V_{IH}	HIGH Level Input Voltage		2.7–3.6	2.0		V
V_{IL}	LOW Level Input Voltage		2.7–3.6		0.8	V
V_{OH}	HIGH Level Output Voltage	I_{OH} = −100 µA	2.7–3.6	V_{CC} − 0.2		V
		I_{OH} = −12 mA	2.7	2.2		V
		I_{OH} = −18 mA	3.0	2.4		V
		I_{OH} = −24 mA	3.0	2.2		V
V_{OL}	LOW Level Output Voltage	I_{OL} = 100 µA	2.7–3.6		0.2	V
		I_{OL} = 12 mA	2.7		0.4	V
		I_{OL} = 16 mA	3.0		0.4	V
		I_{OL} = 24 mA	3.0		0.55	V
I_I	Input Leakage Current	0 ≤ V_I ≤ 5.5V	2.7–3.6		±5.0	µA
I_{OZ}	TRI-STATE I/O Leakage	0 ≤ V_O ≤ 5.5V V_I = V_{IH} or V_{IL}	2.7–3.6		±5.0	µA
I_{OFF}	Power-Off Leakage Current	V_I or V_O = 5.5V	0		10	µA
I_{CC}	Quiescent Supply Current	V_I = V_{CC} or GND	2.7–3.6		20	µA
		3.6V ≤ V_I, V_O ≤ 5.5V	2.7–3.6		±20	µA
ΔI_{CC}	Increase in I_{CC} per Input	V_{IH} = V_{CC} −0.6V	2.7–3.6		500	µA

AC Electrical Characteristics

Symbol	Parameter	$T_A = -40°C$ to $+85°C$				Units
		$V_{CC} = 3.3V \pm 0.3V$		$V_{CC} = 2.7V$		
		Min	Max (Note 3)	Min	Max (Note 3)	
f_{max}	Maximum Clock Frequency	170				MHz
t_{PHL} t_{PLH}	Propagation Delay Bus to Bus	1.5 1.5	6.0 6.0	1.5 1.5	7.0 7.0	ns
t_{PHL} t_{PLH}	Propagation Delay Clock to Bus	1.5 1.5	6.7 6.7	1.5 1.5	8.0 8.0	ns
t_{PHL} t_{PLH}	Propagation Delay LE to Bus	1.5 1.5	7.0 7.0	1.5 1.5	8.0 8.0	ns
t_{PZL} t_{PZH}	Output Enable Time	1.5 1.5	7.2 7.2	1.5 1.5	8.2 8.2	ns
t_{PLZ} t_{PHZ}	Output Disable Time	1.5 1.5	7.0 7.0	1.5 1.5	8.0 8.0	ns
t_s	Setup Time	2.5		2.5		ns
t_H	Hold Time	1.5		1.5		ns
t_W	Pulse Width	3.0		3.0		ns
t_{OSHL} t_{OSLH}	Output to Output Skew (Note 2)		1.0 1.0			ns

Note 1: The Maximum AC limits are design target. Actual performance will be specified upon completion of characterization.

Note 2: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH to LOW (t_{OSHL}), or LOW to HIGH (t_{OSLH}).

Dynamic Switching Characteristics

Symbol	Parameter	Conditions	V_{CC} (V)	$T_A = 25°C$ Typical	Units
V_{OLP}	Quiet Output Dynamic Peak V_{OL}	$C_L = 50$ pF, $V_{IH} = 3.3V$, $V_{IL} = 0V$	3.3	0.8	V
V_{OLV}	Quiet Output Dynamic Valley V_{OL}	$C_L = 50$ pF, $V_{IH} = 3.3V$, $V_{IL} = 0V$	3.3	-0.8	V

Capacitance

Symbol	Parameter	Conditions	Typical	Units
C_{IN}	Input Capacitance	$V_{CC} =$ Open, $V_I = 0V$ or V_{CC}	7	pF
$C_{I/O}$	Input/Output Capacitance	$V_{CC} = 3.3V$, $V_I = 0V$ or V_{CC}	8	pF
C_{PD}	Power Dissipation Capacitance	$V_{CC} = 3.3V$, $V_I = 0V$ or V_{CC}, $F = 10$ MHz	20	pF